

# 1MBI2400VC-120P

**IGBT Modules**

## IGBT MODULE (V series) 1200V / 2400A / 1 in one package

### ■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	$V_{CES}$		1200	V	
Gate-Emitter voltage	$V_{GES}$		±20	V	
Collector current	$I_c$	Continuous	$T_c=25^\circ\text{C}$	3600	A
			$T_c=100^\circ\text{C}$	2400	
	$I_{cp}$	1ms	4800		
	$-I_c$		2400		
	$-I_{c\ pulse}$	1ms	4800		
Collector power dissipation	$P_c$	1 device	13630	W	
Junction temperature	$T_j$		175	°C	
Operating junction temperature (under switching conditions)	$T_{jop}$		150		
Storage temperature	$T_{stg}$		-40 ~ +150		
Isolation voltage	Between terminal and copper base *1	$V_{iso}$	AC : 1min.	4000	VAC
Screw torque *2	Mounting	M6	5.75	Nm	
	Main Terminals	M8	10		
	Sense Terminals	M4	2.5		

(\*1) All terminals should be connected together when isolation test will be done.

(\*2) Recommendable Value :Mounting 4.25~5.75 Nm (M6) , Main Terminals 8~10 Nm (M8) , Sense Terminals 1.7~2.5 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	$I_{CES}$	$V_{GE} = 0V, V_{CE} = 1200V$	-	-	1.0	mA	
Gate-Emitter leakage current	$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	3200	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20V, I_c = 2400mA$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (main terminal)	$V_{GE} = 15V$ $I_c = 2400A$	$T_j = 25^\circ C$	-	2.02	2.31	V
			$T_j = 125^\circ C$	-	2.32	-	
			$T_j = 150^\circ C$	-	2.42	-	
	$V_{CE(sat)}$ (chip)		$T_j = 25^\circ C$	-	1.70	1.95	
			$T_j = 125^\circ C$	-	2.00	-	
			$T_j = 150^\circ C$	-	2.10	-	
Internal gate resistance	Int Rg		-	0.94	-	$\Omega$	
Input capacitance	$C_{ies}$	$V_{CE} = 10V, V_{GE} = 0V, f = 1MHz$	-	208	-	nF	
Turn-on	$t_{on}$	$V_{CC} = 600V, I_c = 2400A$ $L_m = 56nH, V_{GE} = \pm 15V, T_j = 125^\circ C$	-	3.15	-	$\mu s$	
	$t_r$		-	0.97	-		
Turn-off	$t_{off}$	$R_{gon} = 1.8 \Omega$	-	1.93	-		
	$t_f$	$R_{goff} = 0.22 \Omega$	-	0.24	-		
Forward on voltage	$V_F$ (main terminal)	$V_{GE} = 0V$ $I_F = 2400A$	$T_j = 25^\circ C$	-	2.02	2.31	V
			$T_j = 125^\circ C$	-	2.17	-	
			$T_j = 150^\circ C$	-	2.12	-	
	$V_F$ (chip)		$T_j = 25^\circ C$	-	1.70	1.95	
			$T_j = 125^\circ C$	-	1.85	-	
			$T_j = 150^\circ C$	-	1.80	-	
Reverse recovery time	$t_{rr}$	$I_F = 2400A, T_j = 125^\circ C$	-	0.44	-	$\mu s$	
Lead resistance, terminal-chip	$R_{lead}$		-	0.134	-	m $\Omega$	

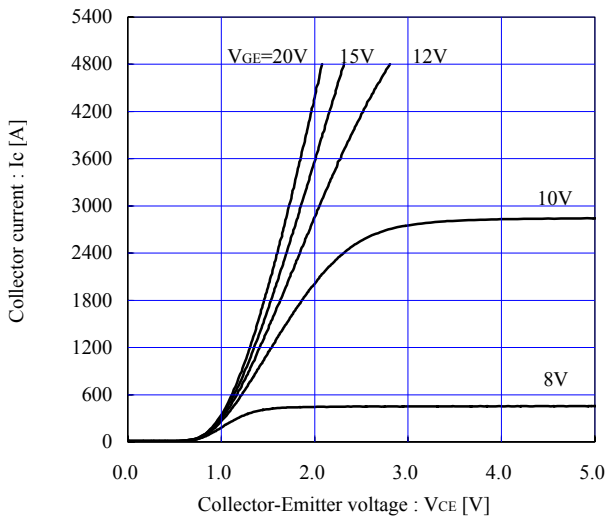
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance	$R_{th(j-c)}$	IGBT	-	-	0.0110	$^\circ C/W$
		FWD	-	-	0.0180	
Contact Thermal resistance	$R_{th(c-f)}$	with Thermal Compound(*)	-	0.0060	-	

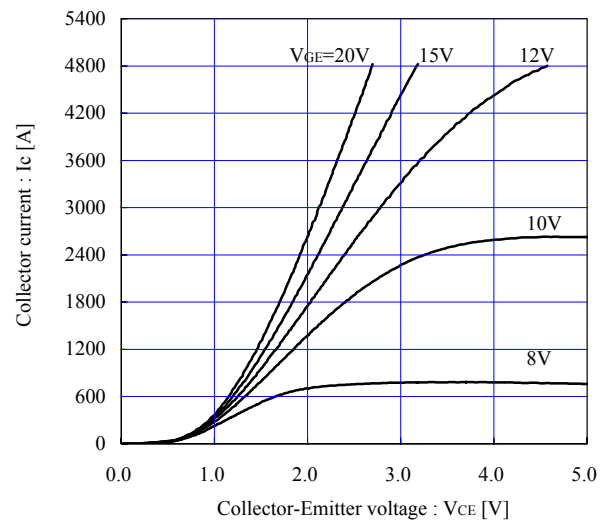
\* This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

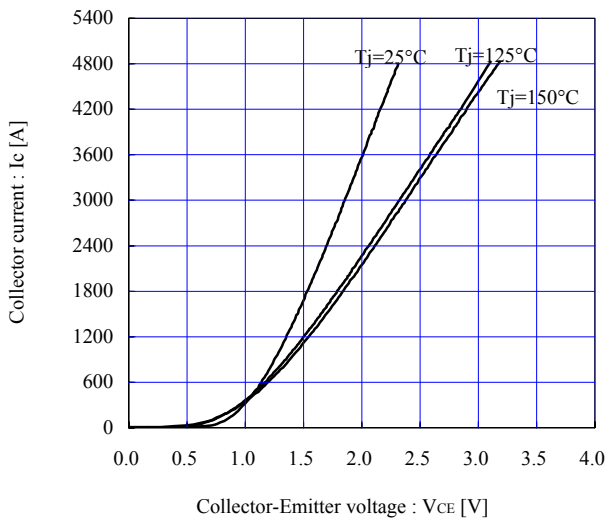
Collector current vs. Collector-Emmitter voltage (typ.)  
Tj=25°C, chip



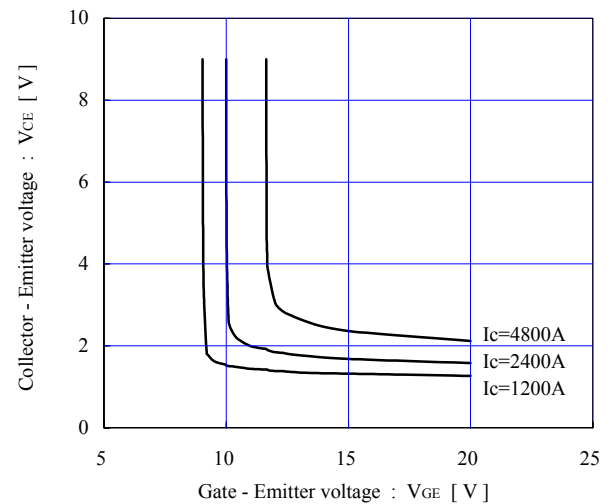
Collector current vs. Collector-Emmitter voltage (typ.)  
Tj= 150°C, chip



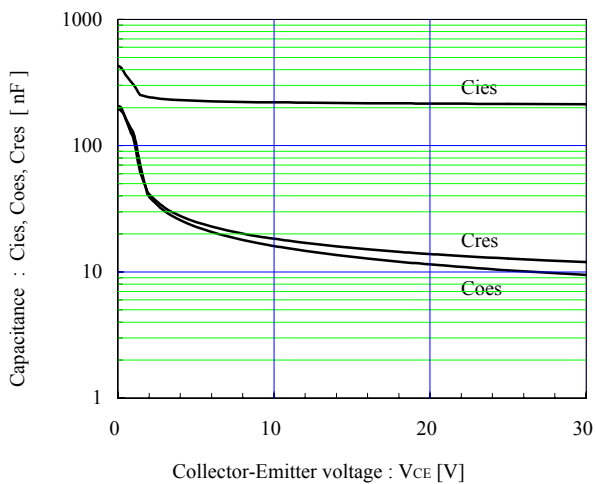
Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)  
VGE=+15V, chip



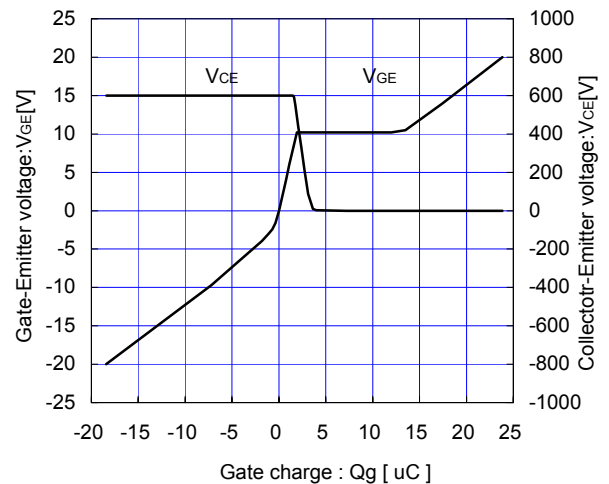
Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)  
Tj=25°C, chip



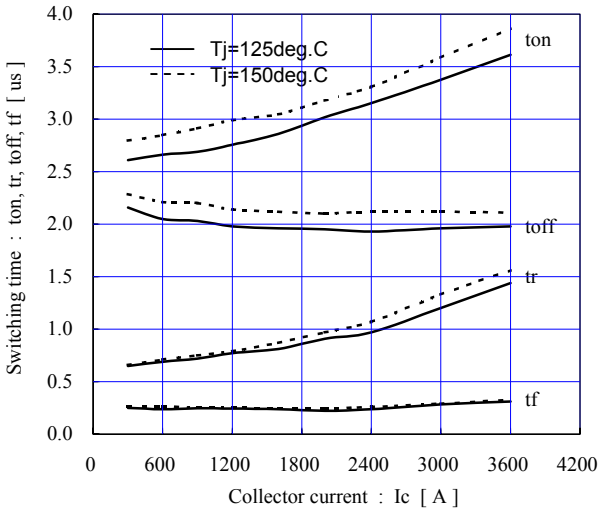
Capacitance vs. Collector-Emmitter voltage (typ.)  
VGE=0V, f= 1MHz, Tj= 25°C



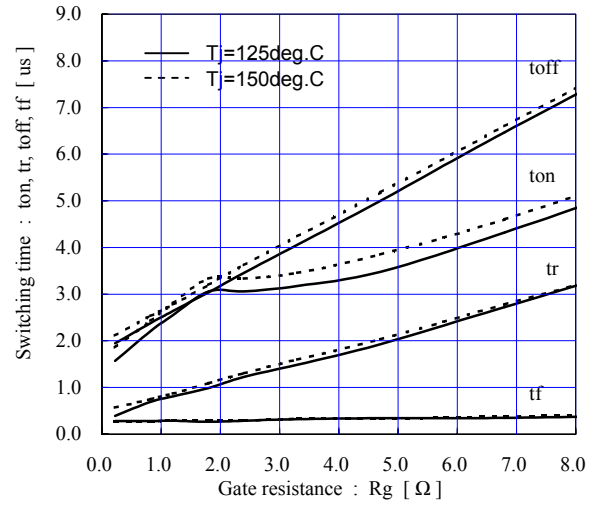
Dynamic Gate charge (typ.)  
Tj= 25°C



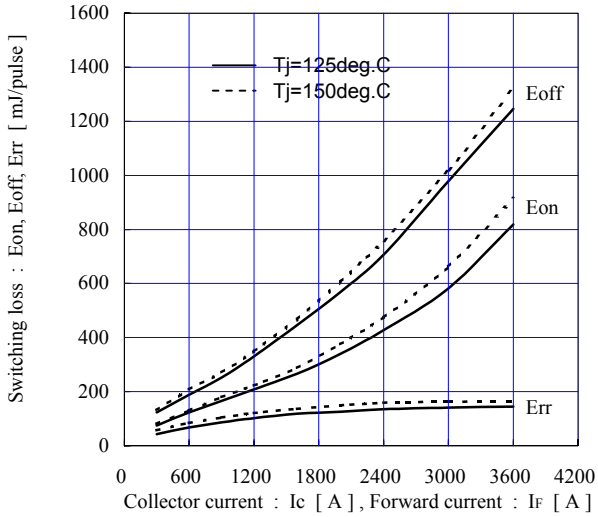
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_{gon}=1.8\Omega, R_{goff}=0.22\Omega$



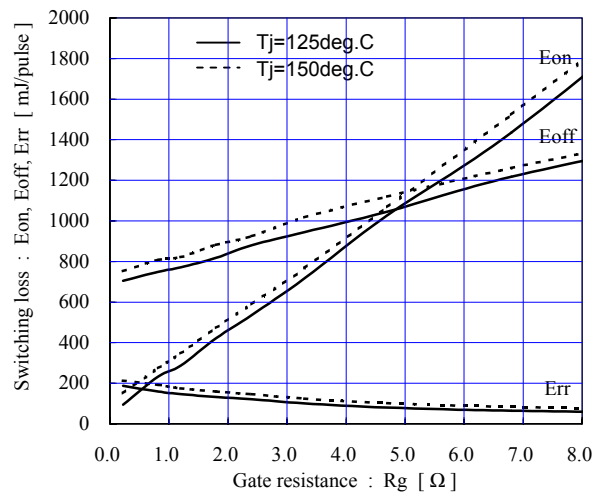
Switching time vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=2400A, V_{GE}=\pm 15V$



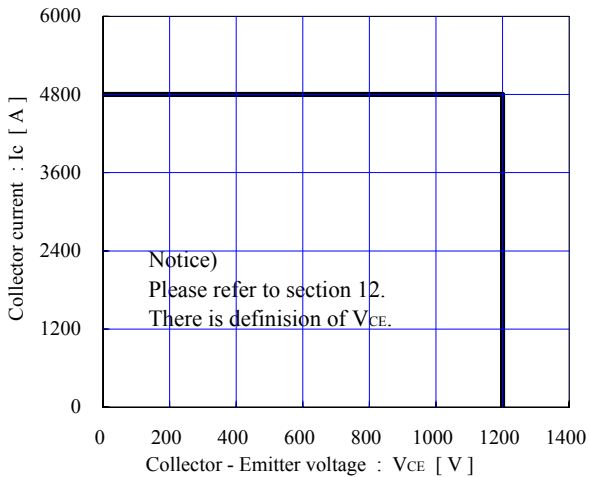
Switching loss vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_{gon}=1.8\Omega, R_{goff}=0.22\Omega$



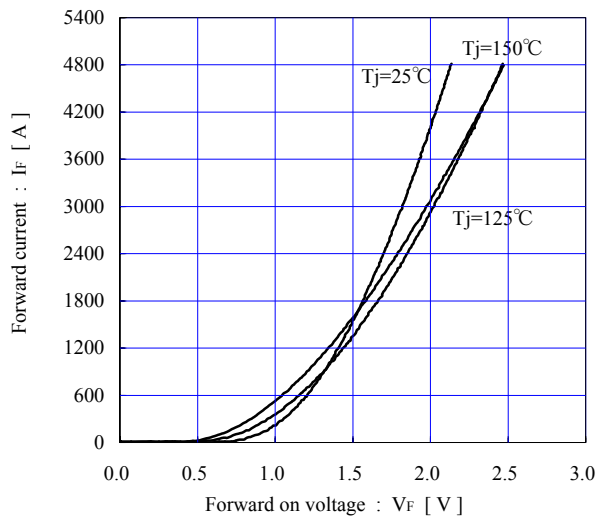
Switching loss vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=2400A, V_{GE}=\pm 15V$



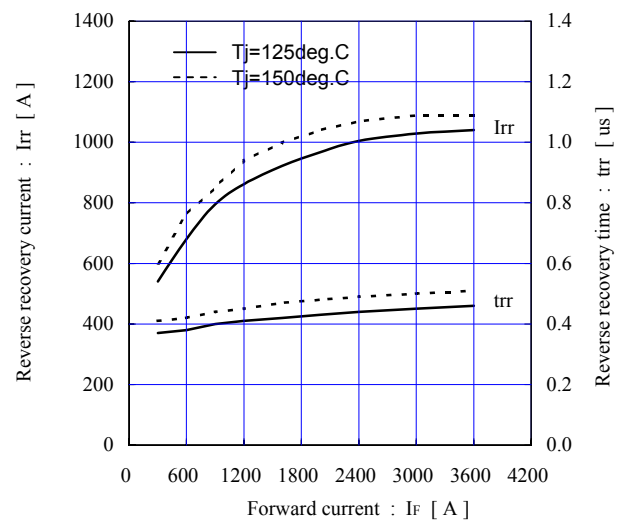
Reverse bias safe operating area (max.)  
 $\pm V_{GE}=15V, T_j=150\text{C}$



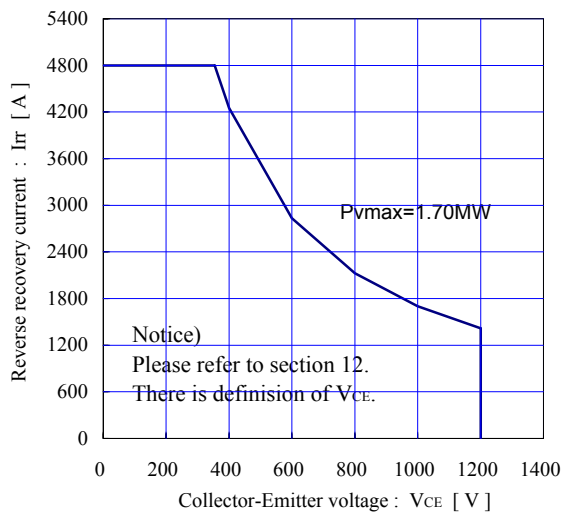
Forward current vs. Forward on voltage (typ.)  
chip



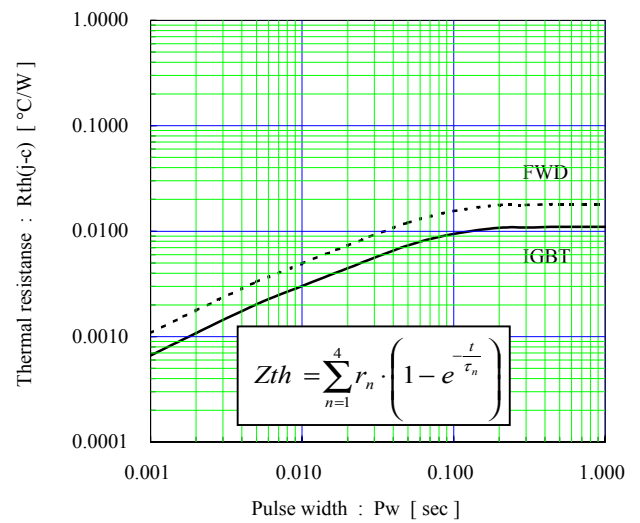
Reverse recovery characteristics (typ.)  
Vcc=600V, VGE=±15V, Rgon=1.8 Ω



FWD safe operating area (max.)  
Tj=150°C

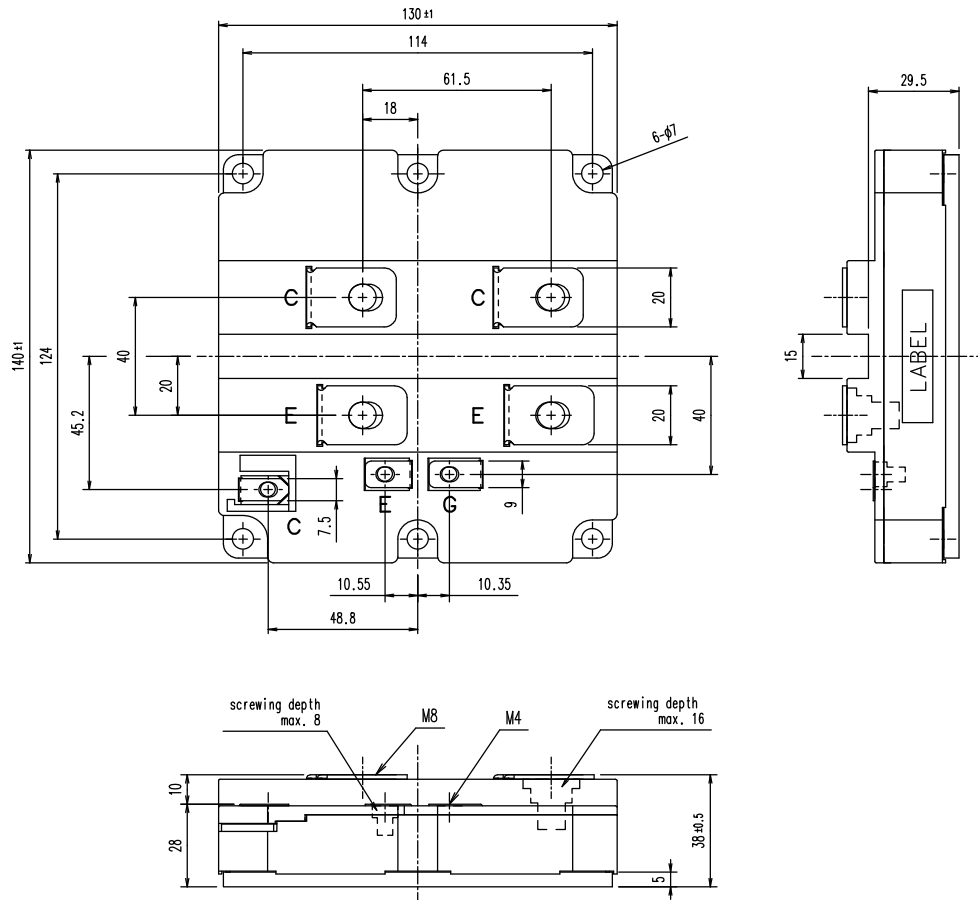


Transient thermal resistance (max.)

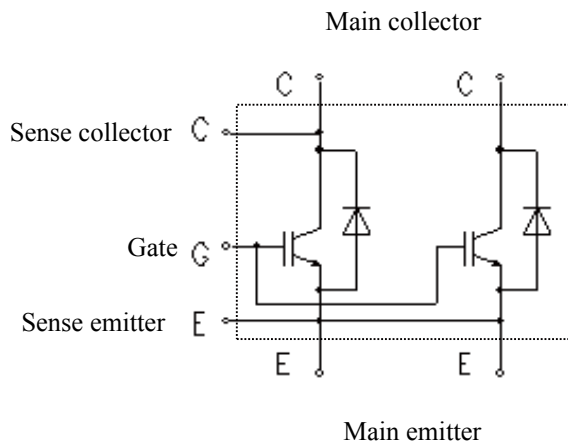


	IGBT	FWD
r1	0.00124	0.00200
r2	0.00424	0.00695
r3	0.00304	0.00498
r4	0.00247	0.00407
τ1	0.0024	0.0024
τ2	0.0359	0.0356
τ3	0.0628	0.0637
τ4	0.0742	0.0734

■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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